

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.1	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	62.5	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance		$V_{GS}=10V, I_D=12A$		50	60	$m\Omega$
		$V_{GS}=4.5V, I_D=8A$		65	75	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=6A$		10		S
Source-drain voltage	V_{SD}	$I_S=12A$			1.28	V

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	960	-	pF
Output capacitance	C_{oss}		-	181	-	
Reverse transfer capacitance	C_{rss}		-	162	-	

Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=25V$	-	15	-	nC
Gate - Source charge	Q_{gs}	$I_D=6A$	-	5.2	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=10V$	-	5.4	-	

Note: ① ;





Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Avalanche Measurement Circuit



Dimensions TO-252

Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

